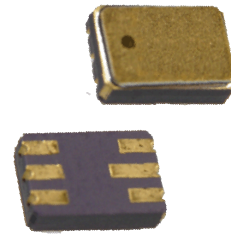


Surface Mount Dual PNP Transistor

2N5796U (TX, TXV)



Features:

- Ceramic 6 pin surface mount package
- Small package to minimize circuit board area
- Hermetically sealed
- Electrical performance similar to dual 2N2907A
- Processed per MIL-PRF-19500/496

Description:

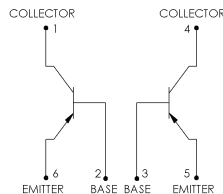
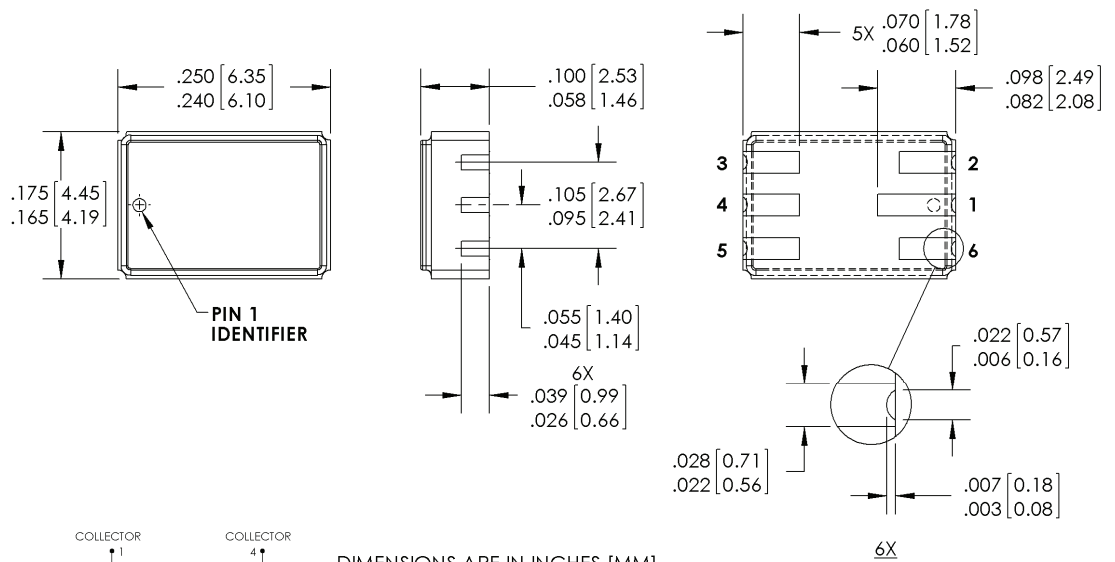
The 2N5796U (TX, TXV) are hermetically sealed, ceramic surface mount devices, consisting of two individual silicon PNP transistors. The six pin ceramic package is ideal for designs where board space and device weight are important design considerations.

Typical screening and lot acceptance tests are per MIL-PRF-19500/496. The burn-in condition is $V_{CB} = 30\text{ V}$, $P_D = 300\text{ mW}$ each transistor, $T_A = 25^\circ\text{C}$. Refer to MIL-PRF-19500/496 for complete requirements.

When ordering parts without processing, do not use the TX or TXV suffix.

Applications:

- General switching
- Amplification
- Signal processing
- Radio transmission
- Logic gates



Pin #	LED	Pin #	Transistor
3	Base	2	Base
4	Collector	1	Collector
5	Emitter	6	Emitter

General Note
TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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Surface Mount Dual PNP Transistor

2N5796U (TX, TXV)



Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)	
Collector-Emitter Voltage	60 V
Collector-Base Voltage	60 V
Emitter-Base Voltage	5 V
Collector Current-Continuous	600 mA
Operating Junction Temperature (T_J)	-65°C to $+200^\circ\text{C}$
Storage Junction Temperature (T_{stg})	-65°C to $+200^\circ\text{C}$
Power Dissipation @ $T_A = 25^\circ\text{C}$	0.5 W
Power Dissipation @ $T_c = 25^\circ\text{C}$	0.6 W ⁽¹⁾
Soldering Temperature (vapor phase reflow for 30 seconds)	215° C
Soldering Temperature (heated collet for 5 seconds)	260° C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)					
SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
OFF CHARACTERISTICS					
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	75			$I_C = 10\ \mu\text{A}$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	60		V	$I_C = 10\ \text{mA}^{(1)}$
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	5		V	$I_E = 10\ \mu\text{A}$
I_{CBO1}	Collector-Base Cutoff Current		10	nA	$V_{CB} = 50\ \text{V}$
I_{CBO2}	Collector-Base Cutoff Current		10	μA	$V_{BC} = 50\ \text{V}, T_A = 150^\circ\text{C}$
I_{EBO}	Emitter-Base Cutoff Current		100	nA	$V_{EB} = 3\ \text{V}$
h_{FE1}	Forward-Current Transfer Ratio	75		-	$V_{CE} = 10\ \text{V}, I_C = 100\ \mu\text{A}$
h_{FE2}		100		-	$V_{CE} = 10\ \text{V}, I_C = 1.0\ \text{mA}$
h_{FE3}		100		-	$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}^{(1)}$
h_{FE4}		100	300	-	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}^{(1)}$
h_{FE5}		50		-	$V_{CE} = 10\ \text{V}, I_C = 300\ \text{mA}^{(1)}$
h_{FE6}		50		-	$V_{CE} = 1.0\ \text{V}, I_C = 150\ \text{mA}^{(1)}$
h_{FE7}		40		-	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}, T_A = -55^\circ\text{C}^{(1)}$

Note:

1. Pulsed Test: Pulse Width = $300\ \mu\text{s} \pm 50$, 1-2 % Duty Cycle

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Surface Mount Dual PNP Transistor

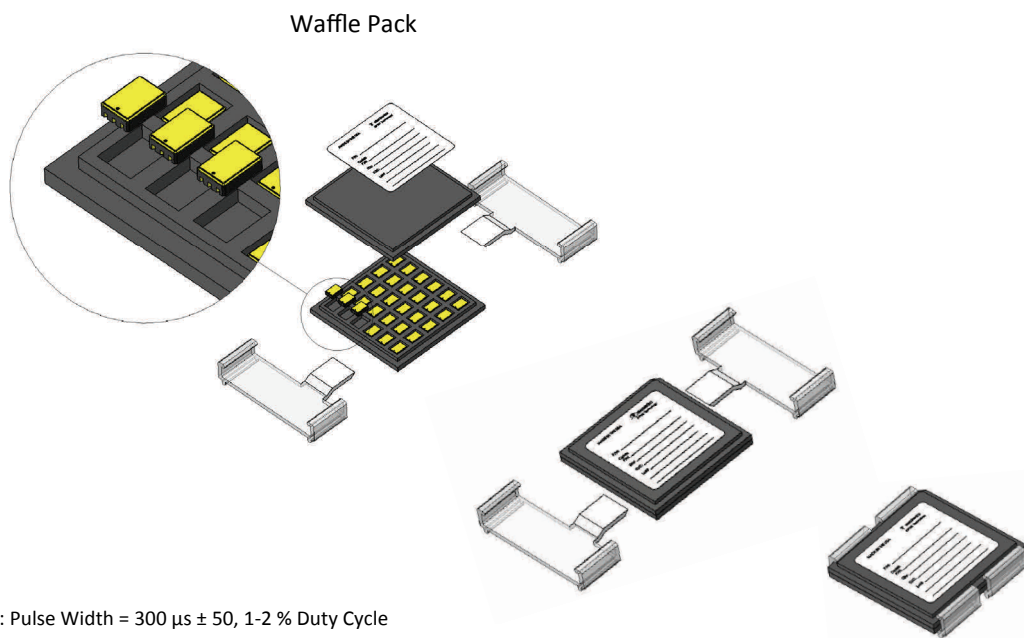
2N5796U (TX, TXV)



Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Off Characteristics continued					
V _{CE(SAT)1}	Collector-Emitter Saturation Voltage		0.4	V	I _C = 150 mA, I _B = 15 mA ⁽¹⁾
V _{CE(SAT)2}	Collector-Emitter Saturation Voltage		1.6	V	I _C = 500 mA, I _B = 50 mA ⁽¹⁾
V _{BE(SAT)1}	Base-Emitter Saturation Voltage		1.3	V	I _C = 150 mA, I _B = 15 mA ⁽¹⁾
V _{BE(SAT)1}	Base-Emitter Saturation Voltage		2.6	V	I _C = 500 mA, I _B = 50 mA ⁽¹⁾
h _{fe}	Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio	2	10		V _{CE} = 20 V, I _C = 20 mA, f = 100 MHz
C _{obo}	Open Circuit Output Capacitance		8	pF	V _{CB} = 10 V, I _E = 0, 100 kHz ≤ f ≤ 1 MHz
C _{ibo}	Input Capacitance (output open)		25	pF	V _{EB} = 2.0 V, I _E = 0, 100 kHz ≤ f ≤ 1 MHz
t _{on}	Turn-on Time		50	ns	V _{CC} = 30 V, I _C = 150 mA, I _{B1} = 15 mA, PW = 200 ns
t _{off}	Turn-off Time		140	ns	V _{CC} = 30 V, I _C = 150 mA, I _{B1} = I _{B2} = 15 mA, PW = 200 ns

Standard Packaging:



Note:

1. Pulsed Test: Pulse Width = 300 μs ± 50, 1-2 % Duty Cycle

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